

Description

The RST4028EK uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It is ESD protected. It can be used in a wide variety of applications.

General Features

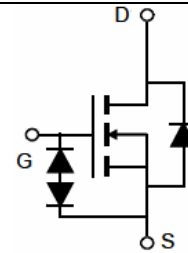
- $V_{DS} = 40V, I_D = 28A$
 $R_{DS(ON)} < 28m\Omega @ V_{GS} = 10V$
 $R_{DS(ON)} < 35m\Omega @ V_{GS} = 4.5V$
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation
- ESD protected

Application

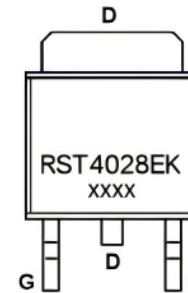
- Load switching
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

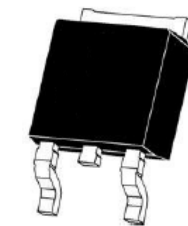
100% ΔV_d s TESTED!



Schematic diagram



Marking and pin assignment



TO-252-2L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
RST4028EK	RST4028EK	TO-252-2L	Ø330mm	12mm	2500 units

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	28	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D (100^\circ C)$	19.8	A
Pulsed Drain Current	I_{DM}	112	A
Maximum Power Dissipation	P_D	50	W
Derating factor		0.33	W/ $^\circ C$
Single pulse avalanche energy (Note 5)	E_{AS}	64	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

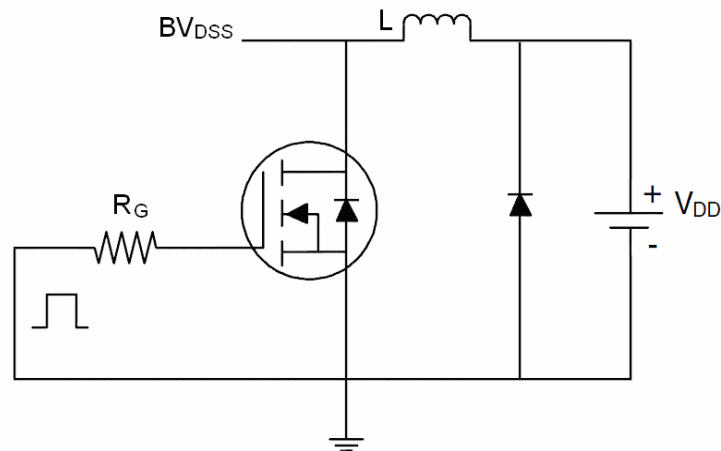
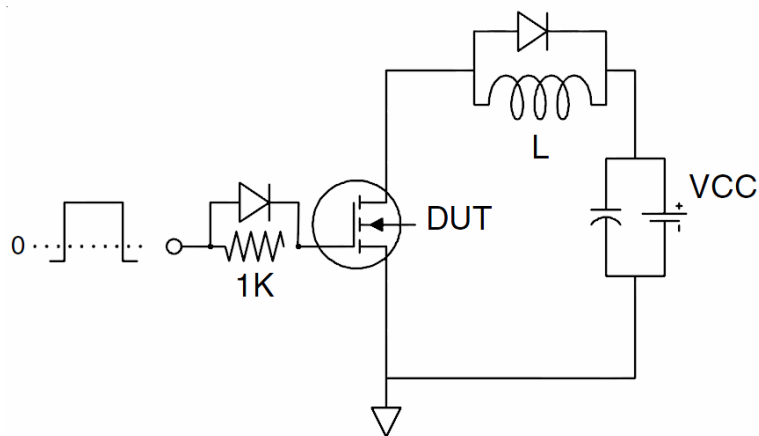
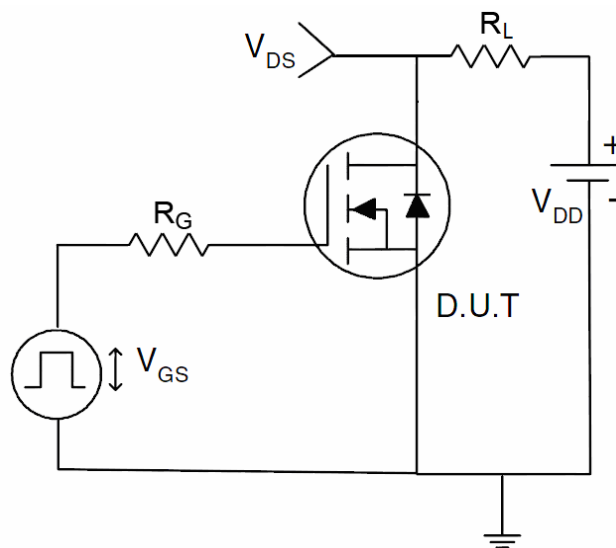
Thermal Resistance, Junction-to-Case (Note 2)	$R_{\theta JC}$	3	$^\circ C/W$
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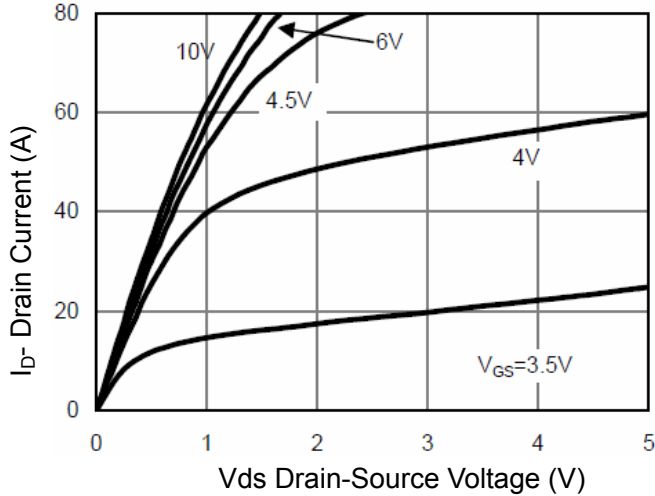
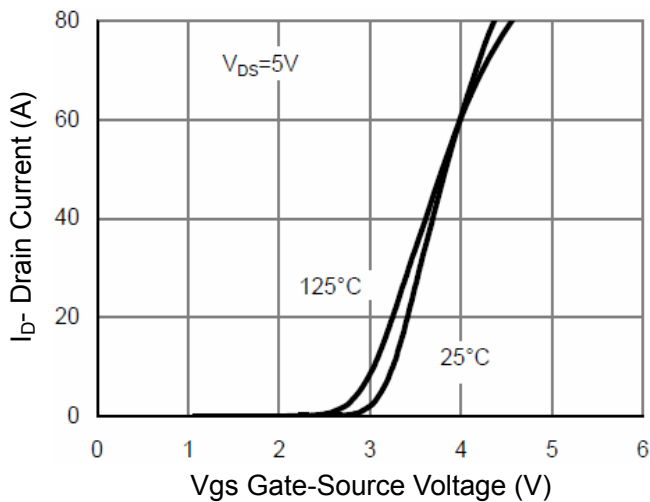
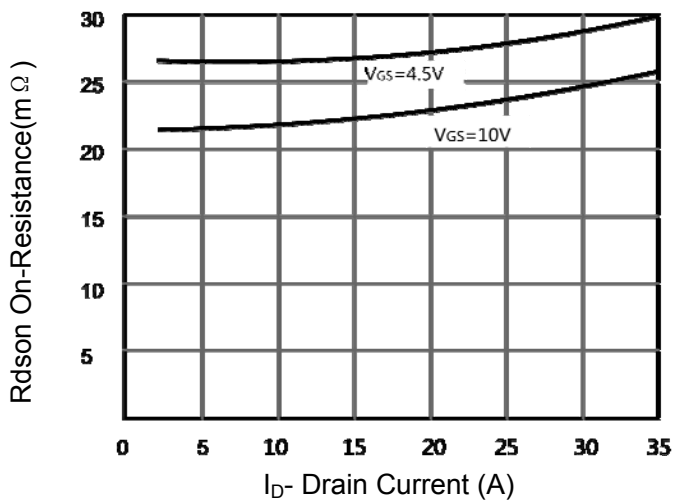
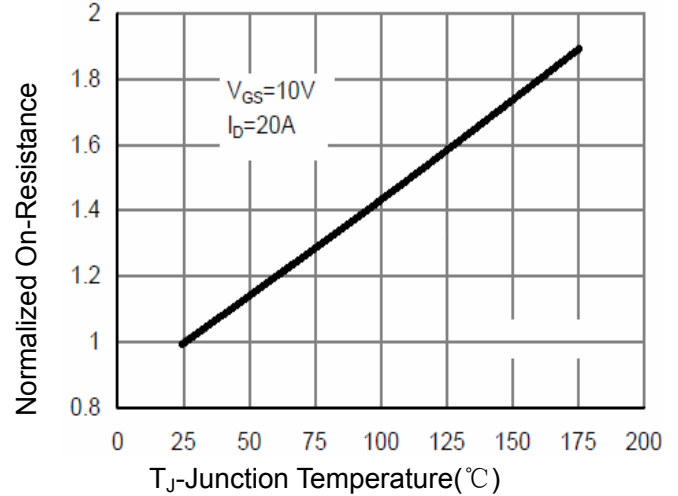
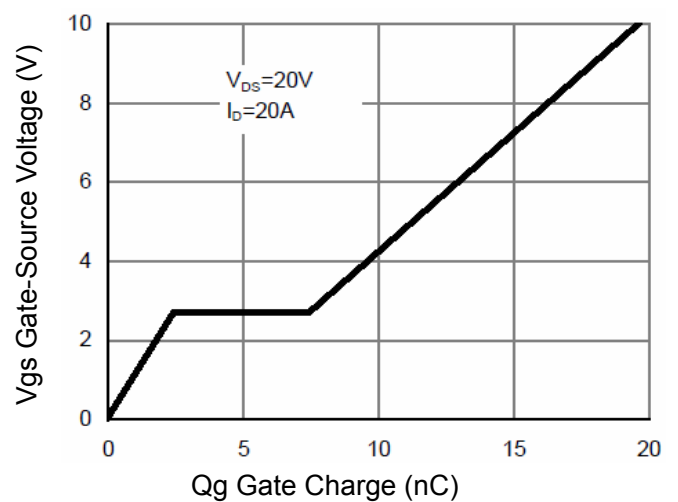
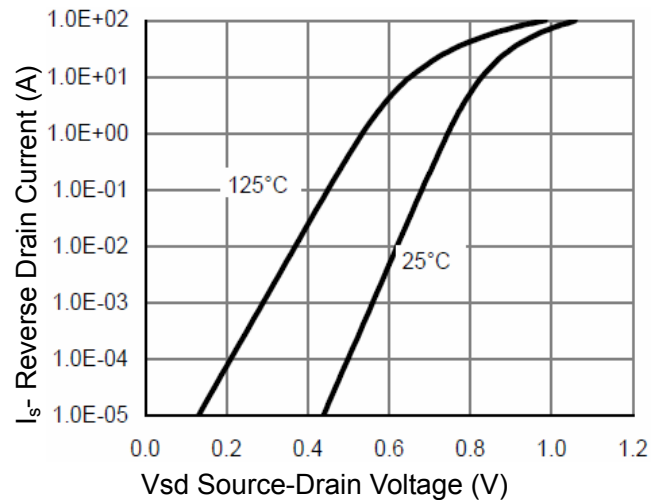
Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

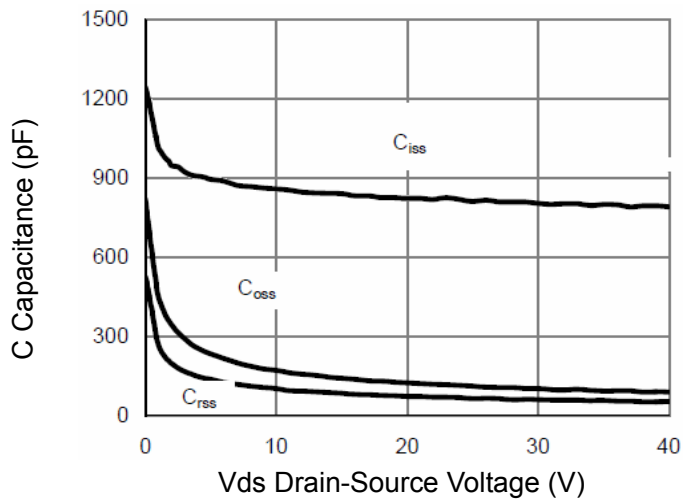
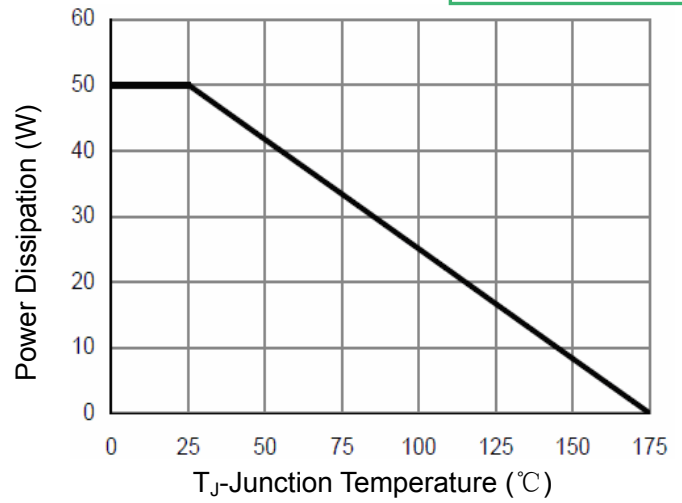
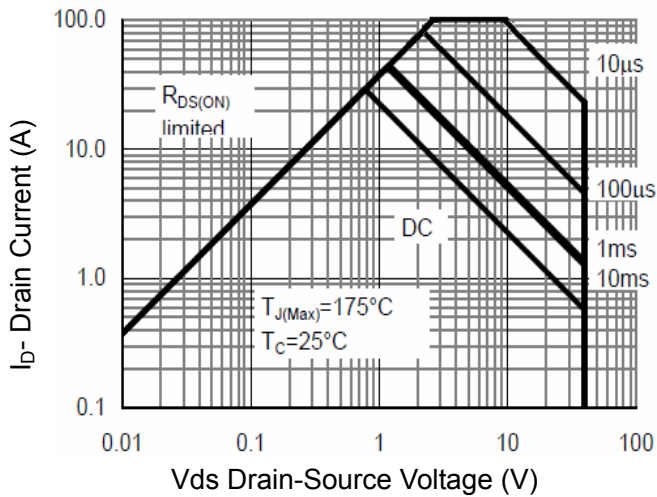
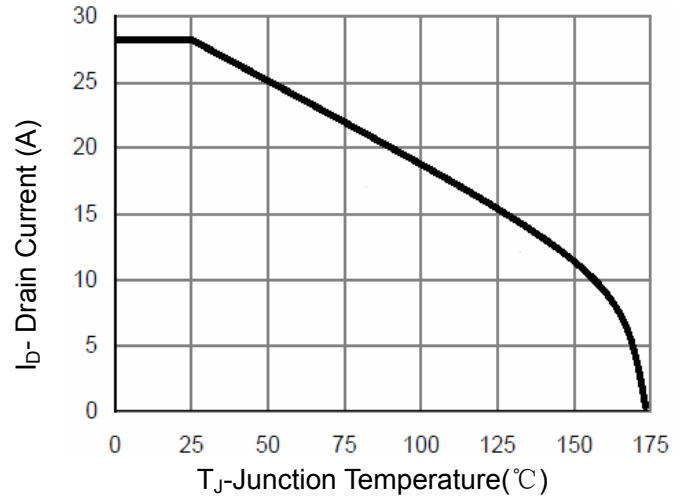
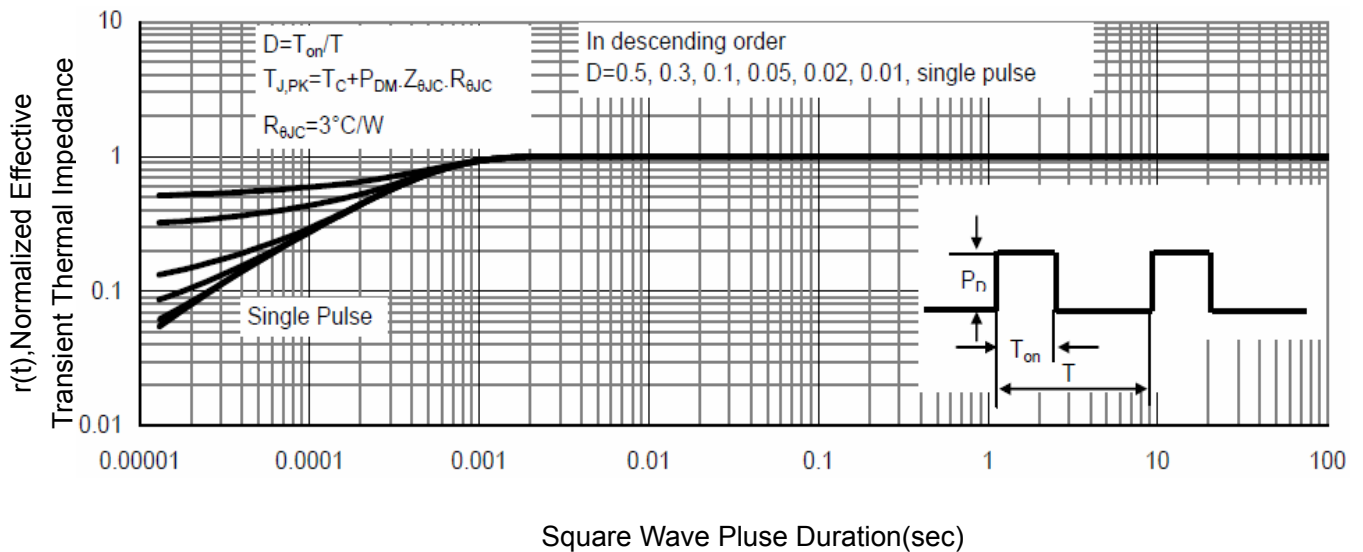
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	40	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±10	μA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.0	1.3	2.2	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	21.8	28	mΩ
		V _{GS} =4.5V, I _D =20A		27.3	35	
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =20A	15	-	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C _{iss}	V _{DS} =20V, V _{GS} =0V, F=1.0MHz	-	817	-	PF
Output Capacitance	C _{oss}		-	100	-	PF
Reverse Transfer Capacitance	C _{rss}		-	83	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =20V, R _L =1Ω V _{GS} =10V, R _G =3Ω	-	5.5	-	nS
Turn-on Rise Time	t _r		-	11	-	nS
Turn-Off Delay Time	t _{d(off)}		-	25	-	nS
Turn-Off Fall Time	t _f		-	6	-	nS
Total Gate Charge	Q _g	V _{DS} =20V, I _D =20A, V _{GS} =10V	-	19.9		nC
Gate-Source Charge	Q _{gs}		-	2.2		nC
Gate-Drain Charge	Q _{gd}		-	6		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V, I _S =28A	-		1.2	V
Diode Forward Current ^(Note 2)	I _S		-	-	28	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 20A di/dt = 100A/μs ^(Note3)	-	12	-	nS
Reverse Recovery Charge	Q _{rr}		-	24	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

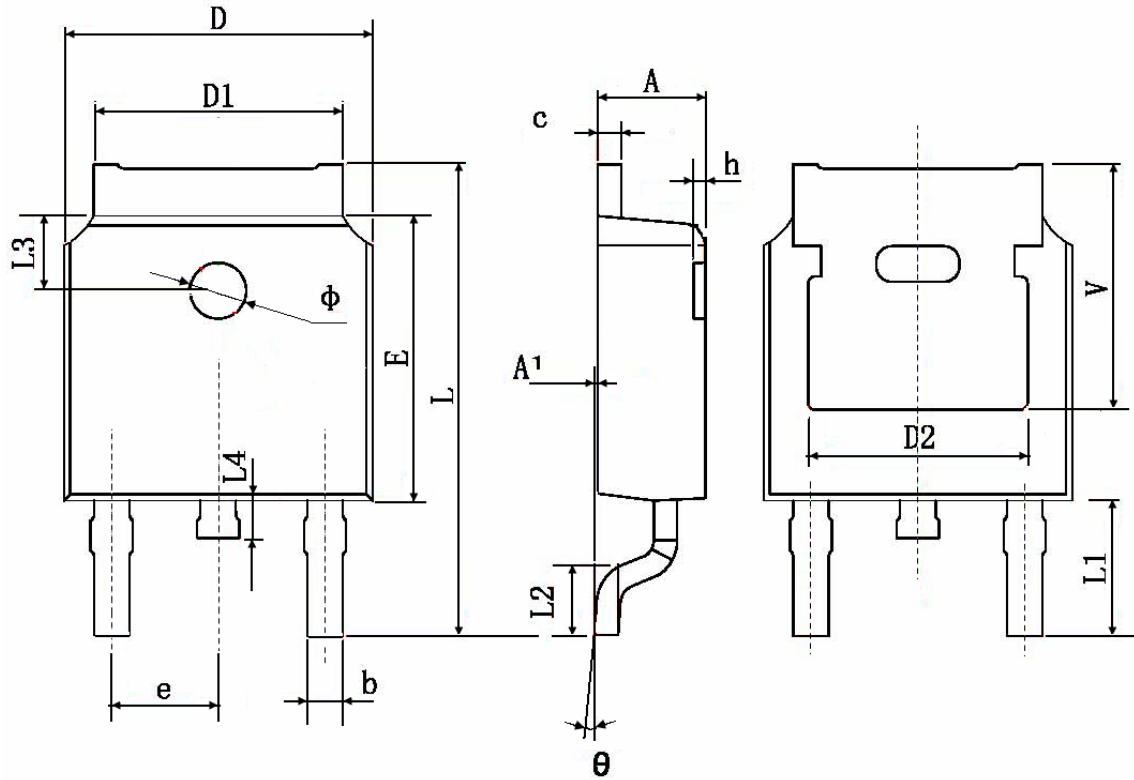
Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. E_{AS} condition : $T_J=25^{\circ}\text{C}, V_{DD}=20V, V_G=10V, L=0.5\text{mH}, R_g=25\Omega$,

Test circuit
1) E_{AS} Test Circuit

2) Gate Charge Test Circuit

3) Switch Time Test Circuit


Typical Electrical and Thermal Characteristics (Curves)

Figure 1 Output Characteristics

Figure 2 Transfer Characteristics

Figure 3 $R_{DS(on)}$ - Drain Current

Figure 4 $R_{DS(on)}$ -Junction Temperature

Figure 5 Gate Charge

Figure 6 Source- Drain Diode Forward

Pb Free Product

Figure 7 Capacitance vs Vds

Figure 9 Power De-rating

Figure 8 Safe Operation Area

Figure 10 I_D Current De-rating

Figure 11 Normalized Maximum Transient Thermal Impedance

TO-252 Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	